

# NCP81255

## Single-Phase Voltage Regulator with Intel Proprietary Interface for Computing Applications

The NCP81255 is a high-performance, low-bias current, single-phase regulator with integrated power MOSFETs intended to support a wide range of computing applications. The device is able to deliver up to 14 A TDC output current on an adjustable output with Intel proprietary interface interface. Operating in high switching frequency up to 1.2 MHz allows employing small size inductor and capacitors. The controller makes use of ON Semiconductor's patented high performance RPM operation. RPM control maximizes transient response while allowing for smooth transitions between discontinuous-frequency-scaling operation and continuous-mode full-power operation. The NCP81255 has an ultra-low offset current monitor amplifier with programmable offset compensation for high-accuracy current monitoring.

### Features

- Auto DCM Operation in High Current Power States
- High Performance RPM Control System
- IMVP8 Intel proprietary interface Support
- Ultra Low Offset IOUT Monitor
- Dynamic VID Feed-Forward
- Programmable Droop Gain
- Zero Droop Capable
- Supports IMVP8 Intel proprietary interface Addresses
- PSYS Input Monitor
- Thermal Monitor
- UltraSonic Operation
- Digitally Controlled Operating Frequency
- QFN40 5 mm × 5 mm Package
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

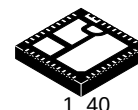
### Applications

- IMVP8 Rail1, Rail3, and Rail4



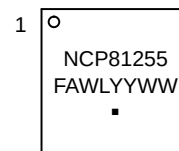
ON Semiconductor®

[www.onsemi.com](http://www.onsemi.com)



QFN40  
CASE 485DY

### MARKING DIAGRAM



NCP81255 = Specific Device Code  
F = Wafer Fab  
A = Assembly Location  
WL = Lot ID  
YY = Year  
WW = Work Week  
▪ = Pb-Free Package

### ORDERING INFORMATION

| Device        | Package            | Shipping†          |
|---------------|--------------------|--------------------|
| NCP81255MNTXG | QFN40<br>(Pb-Free) | 3000 / Tape & Reel |

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

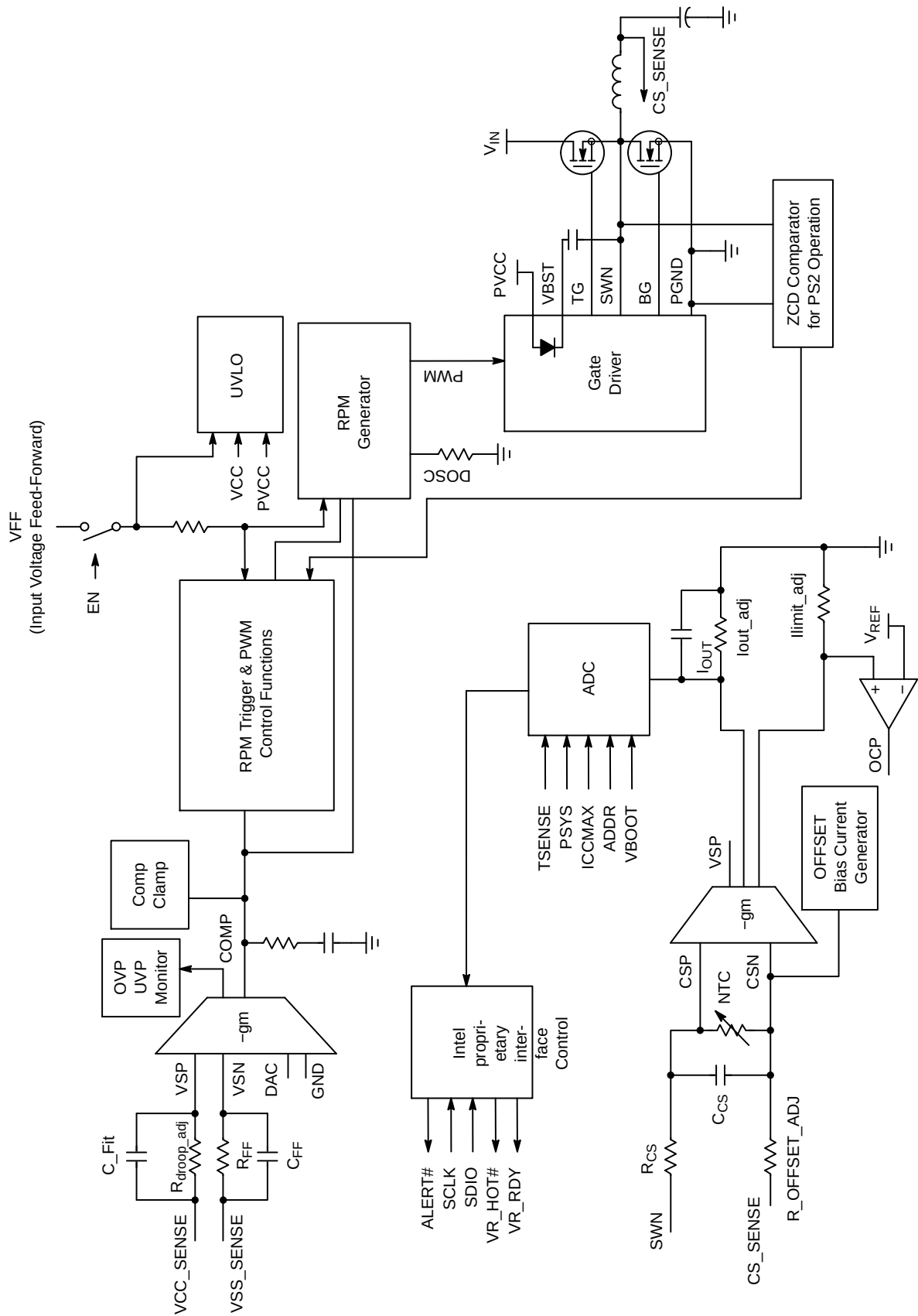


Figure 1. Block Diagram

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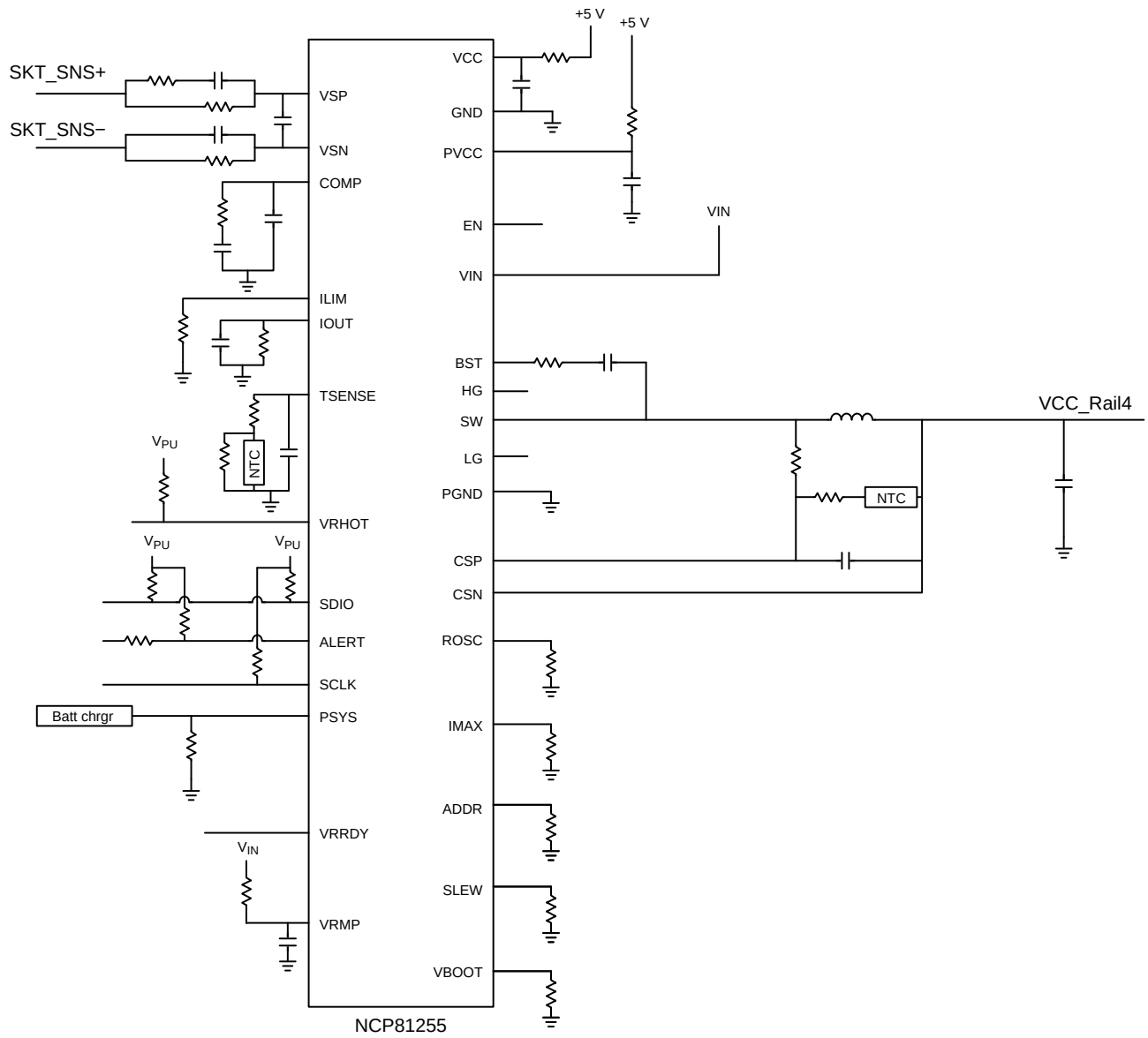
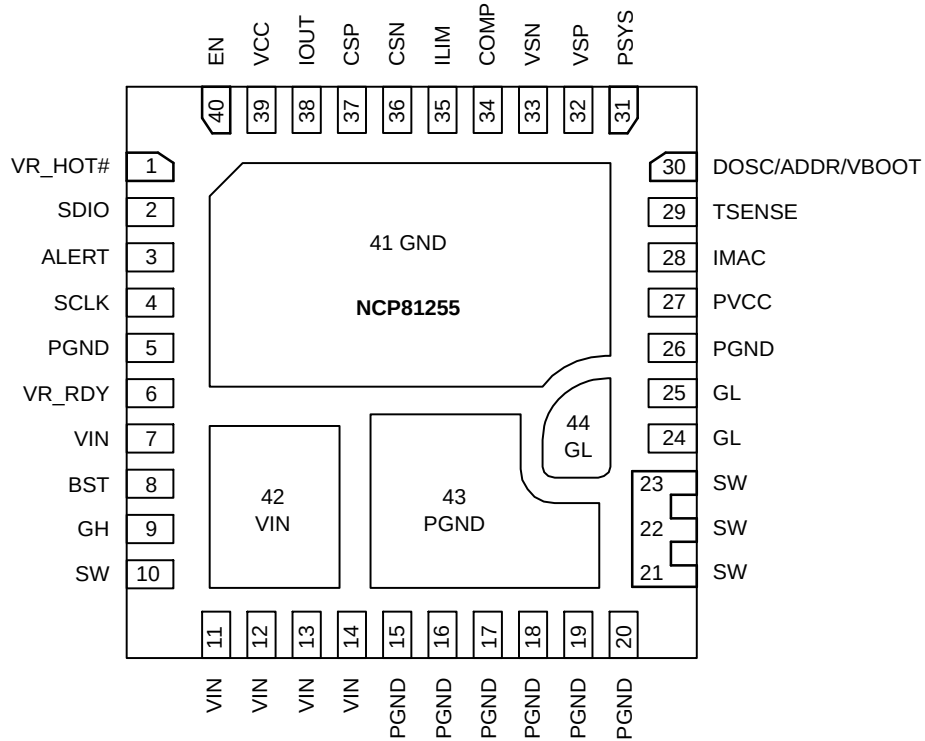


Figure 2. Simplified Application Schematic

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**Figure 3. Pin Configuration**

**Table 1. NCP81255 PIN DESCRIPTIONS**

| Pin No. | Symbol  | Description                                                                                                                 |
|---------|---------|-----------------------------------------------------------------------------------------------------------------------------|
| 1       | VR_HOT# | Thermal Logic Output for Over-Temperature Condition on either TSENSE                                                        |
| 2       | SDIO    | Serial VID Data Interface                                                                                                   |
| 3       | ALERT#  | Serial VID ALERT#                                                                                                           |
| 4       | SCLK    | Serial VID Clock                                                                                                            |
| 5       | PGND    | Power Ground. Power Supply Ground Pins, Connected to Source of Internal LS FET                                              |
| 6       | VR_RDY  | VR_RDY Indicates the Controller is Ready to Accept Intel proprietary interface Commands                                     |
| 7       | VIN     | Input Voltage for HS FET Drain. 22 $\mu$ F or More Ceramic Caps must Bypass this Input to Power Ground. Place Close to Pins |
| 8       | BST     | Provides Bootstrap Voltage for the HS Gate Driver. A Cap is Required from this Pin to SW                                    |
| 9       | GH      | Gate of HS FET                                                                                                              |
| 10      | SW      | Switching Node. Provides a Return Path for the Integrated HS Driver. Internally Connected to the Source of the HS FET       |
| 11      | VIN     | Input Voltage for HS FET Drain. 22 $\mu$ F or More Ceramic Caps must Bypass this Input to Power Ground. Place Close to Pins |
| 12      | VIN     | Input Voltage for HS FET Drain. 22 $\mu$ F or More Ceramic Caps must Bypass this Input to Power Ground. Place Close to Pins |
| 13      | VIN     | Input Voltage for HS FET Drain. 22 $\mu$ F or More Ceramic Caps must Bypass this Input to Power Ground. Place Close to Pins |
| 14      | VIN     | Input Voltage for HS FET Drain. 22 $\mu$ F or More Ceramic Caps must Bypass this Input to Power Ground. Place Close to Pins |
| 15      | PGND    | Power Ground. Power Supply Ground Pins, Connected to Source of Internal LS FET                                              |
| 16      | PGND    | Power Ground. Power Supply Ground Pins, Connected to Source of Internal LS FET                                              |
| 17      | PGND    | Power Ground. Power Supply Ground Pins, Connected to Source of Internal LS FET                                              |
| 18      | PGND    | Power Ground. Power Supply Ground Pins, Connected to Source of Internal LS FET                                              |

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**Table 1. NCP81255 PIN DESCRIPTIONS** (continued)

| Pin No. | Symbol              | Description                                                                                                                                                 |
|---------|---------------------|-------------------------------------------------------------------------------------------------------------------------------------------------------------|
| 19      | PGND                | Power Ground. Power Supply Ground Pins, Connected to Source of Internal LS FET                                                                              |
| 20      | PGND                | Power Ground. Power Supply Ground Pins, Connected to Source of Internal LS FET                                                                              |
| 21      | SW                  | Switch Node. Pins to be Connected to an External Inductor. These Pins are Interconnection between Internal HS and LS FETs                                   |
| 22      | SW                  | Switch Node. Pins to be Connected to an External Inductor. These Pins are Interconnection between Internal HS and LS FETs                                   |
| 23      | SW                  | Switch Node. Pins to be Connected to an External Inductor. These Pins are Interconnection between Internal HS and LS FETs                                   |
| 24      | GL                  | Gate of LS FET                                                                                                                                              |
| 25      | GL                  | Gate of LS FET                                                                                                                                              |
| 26      | PGND                | Power Ground. Power Supply Ground Pins, Connected to Source of Internal LS FET                                                                              |
| 27      | PVCC                | Voltage Supply of Gate Drivers. A 4.7 $\mu$ F or Larger Ceramic Capacitor Bypasses this Input to GND, Placed as Close to the Pin as Possible                |
| 28      | IMAX                | ICCMAX Register Program                                                                                                                                     |
| 29      | TSENSE              | External Temperature Sense Network is Connected to this Pin                                                                                                 |
| 30      | DOSC/ADDR/<br>VBOOT | Programming for $F_{SW}$ , Intel proprietary interface Address, and $V_{BOOT}$ . A Resistor to GND Programs these Values during Start-up, per Look-up Table |
| 31      | PSYS                | System Power Signal Input. A Resistor to Ground Scales this Signal                                                                                          |
| 32      | VSP                 | Differential Output Voltage Sense Positive                                                                                                                  |
| 33      | VSN                 | Differential Output Voltage Sense Negative                                                                                                                  |
| 34      | COMP                | Compensation                                                                                                                                                |
| 35      | ILIM                | Current-Limit Program                                                                                                                                       |
| 36      | CSN                 | Differential Current Sense Negative                                                                                                                         |
| 37      | CSP                 | Differential Current Sense Positive                                                                                                                         |
| 38      | IOUT                | IOUT Gain Program                                                                                                                                           |
| 39      | VCC                 | Power Supply Input Pin of Control Circuits. A 1 $\mu$ F or Larger Ceramic Capacitor Bypasses this Input to Ground, Placed Close to the Controller           |
| 40      | EN                  | Enable                                                                                                                                                      |
| 41      | GND                 | Flag. Analog Ground. Ground of Internal Control Circuits                                                                                                    |
| 42      | VIN                 | Flag. Input Voltage for HS FET Drain. 22 $\mu$ F or More Ceramic Caps must Bypass this Input to Power Ground. Place Close to Pins                           |
| 43      | PGND                | Flag. Power Ground. Power Supply Ground Pins, Connected to Source of Internal LS FET.                                                                       |
| 44      | GL                  | Flag. Gate of LS FET                                                                                                                                        |

Table 2. ABSOLUTE MAXIMUM RATINGS

| Rating                                                                      | Symbol            | Min                   | Max                | Unit |
|-----------------------------------------------------------------------------|-------------------|-----------------------|--------------------|------|
| Power Supply Voltage to PGND                                                | $V_{VIN}$         | –                     | 30                 | V    |
| Switch Node to PGND                                                         | $V_{SW}$          | –0.3                  | 30                 | V    |
| Analog Supply Voltage to GND                                                | $V_{CC}, V_{CCP}$ | –0.3                  | 6.5                | V    |
| BST to PGND                                                                 | BST_PGND          | –0.3                  | 33<br>38 (< 50 ns) | V    |
| BST to SW                                                                   | BST_SW            | –0.3                  | 6.5                | V    |
| GH to SW                                                                    | GH                | –0.3<br>–2 (< 200 ns) | BST + 0.3          | V    |
| GL to GND                                                                   | GL                | –0.3<br>–2 (< 200 ns) | $V_{CCP} + 0.3$    | V    |
| VSN to GND                                                                  | VSN               | –0.3                  | 0.3                | V    |
| IOUT                                                                        | IOUT              | –0.3                  | 2.5                | V    |
| PGND to GND                                                                 | PGND              | –0.3                  | 0.3                | V    |
| Other Pins                                                                  |                   | –0.3                  | $V_{CC} + 0.3$     | V    |
| Latch Up Current: (Note 1)<br>All Pins, Except Digital Pins<br>Digital Pins | $I_{LU}$          | –100<br>–10           | 100<br>10          | mA   |
| Operating Junction Temperature Range                                        | $T_J$             | –40                   | 125                | °C   |
| Operating Ambient Temperature Range                                         | $T_A$             | –40                   | 100                | °C   |
| Storage Temperature Range                                                   | $T_{STG}$         | –40                   | 150                | °C   |
| Thermal Resistance Junction to Board (Note 2)                               | $R_{\theta JB}$   | 8.2                   |                    | °C/W |
| Thermal Resistance Junction to Ambient (Note 2)                             | $R_{\theta JA}$   | 21.8                  |                    | °C/W |
| Power Dissipation at $T_A = 25^\circ\text{C}$ (Note 3)                      | $P_D$             | 4.59                  |                    | W    |
| Moisture Sensitivity Level (Note 4)                                         | MSL               | 3                     |                    | –    |
| ESD Human Body Model                                                        | HBM               | 2,000                 |                    | V    |
| ESD Machine Model                                                           | MM                | 200                   |                    | V    |
| ESD Charged Device Model                                                    | CDM               | 1,000                 |                    | V    |

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Latch up Current per JEDEC standard: JESD78 Class II.
2. The thermal resistance values are dependent on the internal losses split between devices and the PCB heat dissipation. This data is based on a typical operation condition with a 4-layer FR-4 PCB board, which as two, 1-ounce copper internal power and ground planes and 2-ounce copper traces on top and bottom layers with approximately 80% copper coverage. No airflow and no heat sink applied (reference EIA/JEDEC 51.7). It also does not account for other heat sources that may be present on the PCB next to the device in question (such as inductors, resistors, etc.)
3. The maximum power dissipation ( $P_D$ ) is dependent on input voltage, output voltage, output current, external components selected, and PCB layout. The reference data is obtained based on  $T_{JMAX} = 125^\circ\text{C}$  and  $R_{\theta JA} = 21.8^\circ\text{C/W}$ .
4. Moisture Sensitivity Level (MSL): 3 per IPC/JEDEC Standard: J-STD-020D.1.

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**Table 3. ELECTRICAL CHARACTERISTICS**

(Unless otherwise stated:  $-40^{\circ}\text{C} < T_A < 100^{\circ}\text{C}$ ;  $4.75\text{ V} < V_{CC} < 5.25\text{ V}$ ;  $C_{VCC} = 0.1\text{ }\mu\text{F}$ )

| Parameter                         | Test Conditions                                          | Min  | Typ         | Max   | Unit              |
|-----------------------------------|----------------------------------------------------------|------|-------------|-------|-------------------|
| <b>BIAS SUPPLY</b>                |                                                          |      |             |       |                   |
| VCC Quiescent Current             | EN = High                                                | –    | 10          | 12    | mA                |
|                                   | EN = Low                                                 | –    | 20          | 40    | $\mu\text{A}$     |
|                                   | PS3                                                      | –    | –           | 10    | mA                |
|                                   | PS4                                                      | –    | –           | 200   | $\mu\text{A}$     |
| VCC UVLO Threshold                | VCC Rising                                               | –    | –           | 4.5   | V                 |
|                                   | VCC Falling                                              | 4    | –           | –     | V                 |
| VCC UVLO Hysteresis               |                                                          | –    | 275         | –     | mV                |
| VIN UVLO Threshold                | VIN Rising                                               | –    | –           | 4.25  | V                 |
|                                   | VIN Falling                                              | 3    | –           | –     | V                 |
| VIN UVLO Hysteresis               |                                                          | –    | 680         | –     | mV                |
| <b>ENABLE INPUT</b>               |                                                          |      |             |       |                   |
| Enable High Input Leakage Current | Enable = 0                                               | –1.0 | 0           | 1.0   | $\mu\text{A}$     |
| Upper Threshold                   | $V_{\text{UPPER}}$                                       | 0.8  | –           | –     | V                 |
| Lower Threshold                   | $V_{\text{LOWER}}$                                       | –    | –           | 0.3   | V                 |
| Enable Hysteresis                 |                                                          | –    | 300         | –     | mV                |
| Enable Delay Time                 | Measure Time from Enable Transitioning HI to VR_RDY High | –    | –           | 2.5   | ms                |
| <b>DAC SLEW RATE</b>              |                                                          |      |             |       |                   |
| Soft Start Slew Rate              |                                                          | –    | 1/2 SR Fast | –     | mV/ $\mu\text{s}$ |
| Slew Rate Slow                    |                                                          | –    | 1/2 SR Fast | –     | mV/ $\mu\text{s}$ |
| Slew Rate Fast                    |                                                          | –    | 30          | –     | mV/ $\mu\text{s}$ |
| <b>OSCILLATOR</b>                 |                                                          |      |             |       |                   |
| Switching Frequency Range         |                                                          | 600  | –           | 1,200 | KHz               |
| Switching Frequency Accuracy      | $600\text{ KHz} < F_{\text{SW}} < 1.2\text{ MHz}$        | –10  | –           | 10    | %                 |
| <b>ADC</b>                        |                                                          |      |             |       |                   |
| Voltage Range                     |                                                          | 0    | –           | 2     | V                 |
| Total Unadjusted Error (TUE)      |                                                          | –1   | –           | +1    | %                 |
| Differential Non-Linearity (DNL)  | 8-Bit                                                    | –    | –           | 1     | LSB               |
| Power Supply Sensitivity          |                                                          | –    | $\pm 1$     | –     | %                 |
| Conversion Time                   |                                                          | –    | 6           | –     | $\mu\text{s}$     |
| Round Robin                       |                                                          | –    | 55          | –     | $\mu\text{s}$     |
| <b>VR_HOT#</b>                    |                                                          |      |             |       |                   |
| Output Low Voltage                |                                                          | –    | –           | 0.3   | V                 |
| Output Leakage Current            | High Impedance State                                     | –1.0 | –           | 1.0   | $\mu\text{A}$     |
| <b>TSENSE</b>                     |                                                          |      |             |       |                   |
| Alert# Assert Threshold           |                                                          | –    | 491         | –     | mV                |
| Alert# De-Assert Threshold        |                                                          | –    | 513         | –     | mV                |
| VRHOT Assert Threshold            |                                                          | –    | 472         | –     | mV                |
| VRHOT Rising Threshold            |                                                          | –    | 494         | –     | mV                |
| TSENSE Bias Current               |                                                          | 116  | 120         | 124   | $\mu\text{A}$     |

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**Table 3. ELECTRICAL CHARACTERISTICS** (continued)

(Unless otherwise stated:  $-40^{\circ}\text{C} < T_A < 100^{\circ}\text{C}$ ;  $4.75\text{ V} < V_{CC} < 5.25\text{ V}$ ;  $C_{VCC} = 0.1\text{ }\mu\text{F}$ )

| Parameter                                                                 | Test Conditions                                                                                                        | Min   | Typ | Max   | Unit          |
|---------------------------------------------------------------------------|------------------------------------------------------------------------------------------------------------------------|-------|-----|-------|---------------|
| <b>VR_RDY_OUTPUT</b>                                                      |                                                                                                                        |       |     |       |               |
| Output Low Saturation Voltage                                             | $I_{VR\_RDY} = 4\text{ mA}$ ,                                                                                          | –     | –   | 0.3   | V             |
| Rise Time                                                                 | External Pull-Up of $1\text{ k}\Omega$ to $3.3\text{ V}$ ,<br>$C_{TOT} = 45\text{ pF}$ , $\Delta V_o = 10\%$ to $90\%$ | –     | –   | 150   | ns            |
| Fall Time                                                                 | External Pull-Up of $1\text{ k}\Omega$ to $3.3\text{ V}$ ,<br>$C_{TOT} = 45\text{ pF}$ , $\Delta V_o = 90\%$ to $10\%$ | –     | –   | 150   | ns            |
| Output Voltage at Power-Up                                                | VRRDY Pulled Up to $5\text{ V}$ via $2\text{ k}\Omega$                                                                 | –     | –   | 1.2   | V             |
| Output Leakage Current When High                                          | VRRDY = $5.0\text{ V}$                                                                                                 | –1.0  | –   | 1.0   | $\mu\text{A}$ |
| VRRDY Delay (Falling)                                                     | From OCP                                                                                                               | –     | 0   | –     | $\mu\text{s}$ |
| VRRDY Delay (Falling)                                                     | From OVP                                                                                                               | –     | 0.3 | –     | $\mu\text{s}$ |
| <b>DIFFERENTIAL VOLTAGE SENSE AMPLIFIER</b>                               |                                                                                                                        |       |     |       |               |
| Input Bias Current                                                        |                                                                                                                        | –1    | –   | 1     | $\mu\text{A}$ |
| VSP Input Voltage Range                                                   |                                                                                                                        | –0.3  | –   | 3.0   | V             |
| VSN Input Voltage Range                                                   |                                                                                                                        | –0.3  | –   | 0.3   | V             |
| gm                                                                        | VSP = $1.2\text{ V}$                                                                                                   | 1.33  | 1.6 | 1.86  | mS            |
| Open loop Gain                                                            | Load = $1\text{ nF}$ in Series with $1\text{ k}\Omega$ in Parallel<br>with $10\text{ pF}$ to Ground                    | 70    | 73  | –     | dB            |
| Source Current                                                            | Input Differential $-200\text{ mV}$                                                                                    | –     | 280 | –     | $\mu\text{A}$ |
| Sink Current                                                              | Input Differential $200\text{ mV}$                                                                                     | –     | 280 | –     | $\mu\text{A}$ |
| –3dB Bandwidth                                                            | Load = $1\text{ nF}$ in Series with $1\text{ k}\Omega$ in Parallel<br>with $10\text{ pF}$ to Ground                    | –     | 15  | –     | MHz           |
| <b>IOUT</b>                                                               |                                                                                                                        |       |     |       |               |
| Analog Gain Accuracy                                                      |                                                                                                                        | –3    | –   | +3    | %             |
| gm                                                                        |                                                                                                                        | 0.95  | 1.0 | 1.05  | mS            |
| IOUT Output Accuracy                                                      |                                                                                                                        | –140  | –   | 140   | nA            |
| ADC Voltage Range                                                         |                                                                                                                        | 0     | –   | 2.0   | V             |
| ADC Differential Nonlinearity (DNL)                                       | Highest 8-Bits                                                                                                         | –     | –   | 1     | LSB           |
| <b>OUTPUT OVER VOLTAGE &amp; UNDER VOLTAGE PROTECTION (OVP &amp; UVP)</b> |                                                                                                                        |       |     |       |               |
| Over Voltage Threshold                                                    | VSP–VSN–VID Setting                                                                                                    | 360   | –   | 440   | mV            |
| Over Voltage Max Capability                                               |                                                                                                                        | –     | 2   | –     | V             |
| Over Voltage Delay                                                        | VSP Rising to PWMx Low                                                                                                 | –     | 400 | –     | ns            |
| Over Voltage VR_RDY Delay                                                 | VSP Rising to VR_RDY Low                                                                                               | –     | 400 | –     | ns            |
| Under Voltage Threshold                                                   | VSP–VSN Falling                                                                                                        | 225   | 290 | 375   | mV            |
| Under-Voltage Hysteresis                                                  | VSP–VSN Falling/Rising                                                                                                 | –     | 25  | –     | mV            |
| Under-Voltage Blanking Delay                                              | VSP–VSN Falling to VR_RDY Falling                                                                                      | –     | 5   | –     | $\mu\text{s}$ |
| <b>DROOP</b>                                                              |                                                                                                                        |       |     |       |               |
| gm                                                                        |                                                                                                                        | 0.95  | 1.0 | 1.05  | mS            |
| Offset Accuracy                                                           |                                                                                                                        | –1    | –   | 1     | $\mu\text{A}$ |
| Common Mode Rejection                                                     | CS1 Input Referred from $0.5\text{ V}$ to $1.2\text{ V}$                                                               | –     | 80  | –     | dB            |
| <b>OVERCURRENT PROTECTION</b>                                             |                                                                                                                        |       |     |       |               |
| ILIMIT Threshold                                                          |                                                                                                                        | 1.275 | 1.3 | 1.325 | V             |
| ILIMIT Delay                                                              |                                                                                                                        | –     | 500 | –     | ns            |
| ILIMIT Gain                                                               | $I_{LIMIT}/(CSP-CSN)$ , $CSP-CSN = 20\text{ mV}$                                                                       | –     | 1.0 | –     | mS            |
| <b>CSP-CSN ZCD COMPARATOR</b>                                             |                                                                                                                        |       |     |       |               |
| Offset Accuracy                                                           |                                                                                                                        | –1.85 | –   | 1.85  | mV            |



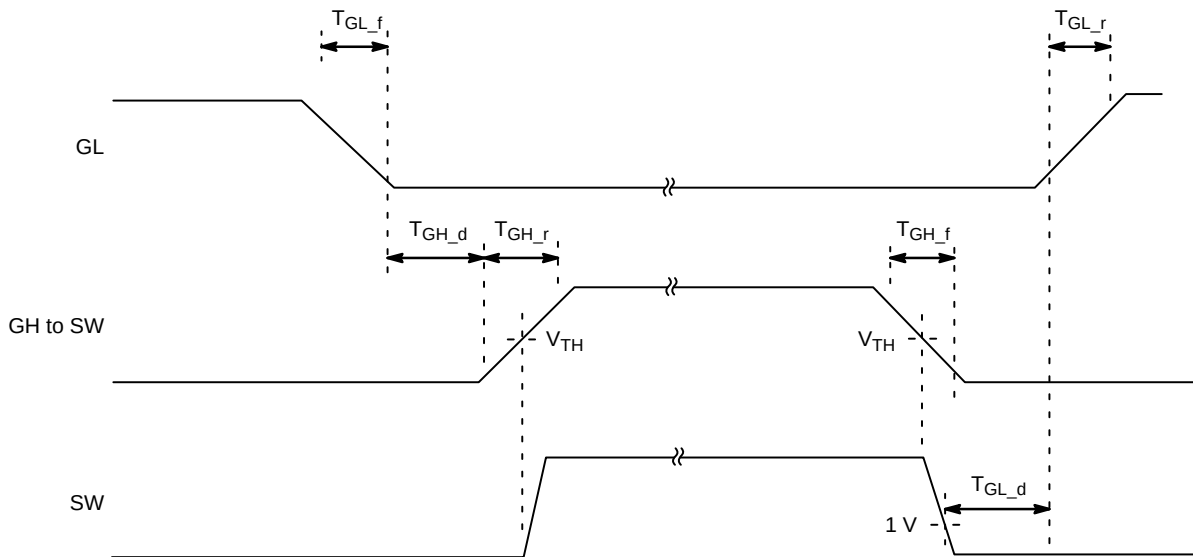
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**Table 3. ELECTRICAL CHARACTERISTICS** (continued)

(Unless otherwise stated:  $-40^{\circ}\text{C} < T_A < 100^{\circ}\text{C}$ ;  $4.75\text{ V} < V_{CC} < 5.25\text{ V}$ ;  $C_{VCC} = 0.1\text{ }\mu\text{F}$ )

| Parameter                         | Test Conditions                                             | Min  | Typ | Max  | Unit       |
|-----------------------------------|-------------------------------------------------------------|------|-----|------|------------|
| <b>SWN ZCD COMPARATOR</b>         |                                                             |      |     |      |            |
| Offset Accuracy                   |                                                             | -1.5 | -   | 1.5  | mV         |
| <b>HIGH-SIDE MOSFET</b>           |                                                             |      |     |      |            |
| Drain-to-Source On Resistance     | $V_{GS} = 4.5\text{ V}$ , $I_D = 10\text{ A}$ , $R_{ON\_H}$ | -    | 8.0 | -    | m $\Omega$ |
| <b>LOW-SIDE MOSFET</b>            |                                                             |      |     |      |            |
| Drain-to-Source On Resistance     | $V_{GS} = 4.5\text{ V}$ , $I_D = 10\text{ A}$ , $R_{ON\_L}$ | -    | 4.0 | -    | m $\Omega$ |
| <b>HIGH-SIDE GATE DRIVE</b>       |                                                             |      |     |      |            |
| Pull-High Drive On Resistance     | $V_{BST} - V_{SW} = 5\text{ V}$ , $R_{DRV\_HH}$             | -    | 1.2 | 2.5  | $\Omega$   |
| Pull-Low Drive On Resistance      | $V_{BST} - V_{SW} = 5\text{ V}$ , $R_{DRV\_HL}$             | -    | 0.8 | 2.0  | $\Omega$   |
| GH Propagation Delay Time         | From GL Falling to GH Rising, $T_{GH\_d}$                   | 15   | 23  | 30   | ns         |
| GH Rise Time                      | $T_{GH\_R}$                                                 | -    | 9   | 15   | ns         |
| GH Fall Time                      | $T_{GH\_F}$                                                 | 4    | 9   | 15   | ns         |
| GH Pull-Down Resistance           | $V_{BST} - V_{SW} = 0\text{ V}$                             | -    | 292 | -    | k $\Omega$ |
| <b>LOW-SIDE GATE DRIVE</b>        |                                                             |      |     |      |            |
| Pull-High Drive On Resistance     | $V_{CCP} - V_{PGND} = 5\text{ V}$ , $R_{DRV\_LH}$           | -    | 0.9 | 2.5  | $\Omega$   |
| Pull-Low Drive On Resistance      | $V_{CCP} - V_{PGND} = 5\text{ V}$ , $R_{DRV\_LL}$           | -    | 0.4 | 1.25 | $\Omega$   |
| GL Propagation Delay Time         | From GH Falling to GL Rising, $T_{GL\_d}$                   | -    | 11  | 30   | ns         |
| GL Rise Time                      | $T_{GL\_R}$                                                 | 6    | 9   | 15   | ns         |
| GL Fall Time                      | $T_{GL\_F}$                                                 | -    | 11  | 15   | ns         |
| <b>SW TO PGND RESISTANCE</b>      |                                                             |      |     |      |            |
| SW to PGND Pull-Down Resistance   | $R_{SW}$ (Note 1)                                           | -    | 2   | -    | k $\Omega$ |
| <b>BOOTSTRAP RECTIFIER SWITCH</b> |                                                             |      |     |      |            |
| Output Low Resistance             | $EN = L$ or $EN = H$ and $DRVL = H$ , $R_{on\_BST}$         | 5    | 13  | 21   | $\Omega$   |

1. Guaranteed by design, not tested in production.
2.  $T_J = 25^{\circ}\text{C}$



NOTE: Timing is referenced to the 10% and the 90% points, unless otherwise stated.

**Figure 4. Driver Timing Diagram**

Table 4. STATE TRUTH TABLE

| State                                                                         | VR_RDY Pin                                                | Error AMP<br>Comp Pin | OVP & UVP       | Method<br>of Reset |
|-------------------------------------------------------------------------------|-----------------------------------------------------------|-----------------------|-----------------|--------------------|
| <b>POR</b><br>0 < VCC < UVLO                                                  | N/A                                                       | N/A                   | N/A             |                    |
| <b>Disabled</b><br>EN < Threshold<br>UVLO > Threshold                         | Low                                                       | Low                   | Disabled        |                    |
| <b>Start-Up Delay &amp; Calibration</b><br>EN > Threshold<br>UVLO > Threshold | Low                                                       | Low                   | Disabled        |                    |
| <b>Soft Start</b><br>EN > Threshold<br>UVLO > Threshold                       | Low                                                       | Operational           | Active/No Latch |                    |
| <b>Normal Operation</b><br>EN > Threshold<br>UVLO > Threshold                 | High                                                      | Operational           | Active/Latching | N/A                |
| <b>Over Voltage</b>                                                           | Low                                                       | N/A                   | DAC + 150 mV    |                    |
| <b>Over Current</b>                                                           | Low                                                       | Operational           | Last DAC Code   |                    |
| <b>Vout = 0 V</b>                                                             | Low: if Reg34h: bit 0 = 0;<br>High: if Reg34h: bit 0 = 1; | Clamped at 0.9 V      | Disabled        |                    |

# NCP81255

## GENERAL

The NCP81255 is a single phase IMVP8 Intel proprietary interface controller with a built in gate driver. The controller makes use of a digitally enhanced high performance current mode RPM control method that provides excellent transient response while minimizing transient aliasing. The average operating frequency is digitally stabilized to remove frequency drift under all continuous mode operating conditions. At light load the NCP81255 automatically transitions into DCM operation to save power.

### Switching Frequency, Intel proprietary interface Address, and Boot Voltage Programming

$F_{SW}$ , address, and VBOOT are during power up on a single pin. A 10  $\mu$ A current is sourced from the pin and the resulting voltage is measured. This is compared with the thresholds and the corresponding values for  $F_{SW}$ , VBOOT, and Intel proprietary interface address are configured. These values are programmed on power up and cannot be changed after the initial power up sequence is complete.

### Serial VID Interface (Intel proprietary interface)

For Intel proprietary interface communication details please contact Intel<sup>®</sup>, Inc.

**Table 5. SWITCHING FREQUENCY**

|    | Resistor         | $F_{SW}$ | Address | VBOOT  |
|----|------------------|----------|---------|--------|
| 1  | 10 k $\Omega$    | 1.2 MHz  | 0       | 0 V    |
| 2  | 13 k $\Omega$    | 1.1 MHz  | 0       | 0 V    |
| 3  | 16 k $\Omega$    | 1.0 MHz  | 0       | 0 V    |
| 4  | 19.2 k $\Omega$  | 900 kHz  | 0       | 0 V    |
| 5  | 22.5 k $\Omega$  | 800 kHz  | 0       | 0 V    |
| 6  | 26 k $\Omega$    | 700 kHz  | 0       | 0 V    |
| 7  | 29.6 k $\Omega$  | 600 kHz  | 0       | 0 V    |
| 8  | 33.5 k $\Omega$  | 1.2 MHz  | 1       | 0 V    |
| 9  | 37.4 k $\Omega$  | 1.1 MHz  | 1       | 0 V    |
| 10 | 41.5 k $\Omega$  | 1.0 MHz  | 1       | 0 V    |
| 11 | 45.8 k $\Omega$  | 900 kHz  | 1       | 0 V    |
| 12 | 50.2 k $\Omega$  | 800 kHz  | 1       | 0 V    |
| 13 | 54.8 k $\Omega$  | 700 kHz  | 1       | 0 V    |
| 14 | 59.5 k $\Omega$  | 600 kHz  | 1       | 0 V    |
| 15 | 64.5 k $\Omega$  | 1.2 MHz  | 2       | 1.05 V |
| 16 | 69.6 k $\Omega$  | 1.1 MHz  | 2       | 1.05 V |
| 17 | 75 k $\Omega$    | 1.0 MHz  | 2       | 1.05 V |
| 18 | 80.6 k $\Omega$  | 900 kHz  | 2       | 1.05 V |
| 19 | 86.5 k $\Omega$  | 800 kHz  | 2       | 1.05 V |
| 20 | 92.6 k $\Omega$  | 700 kHz  | 2       | 1.05 V |
| 21 | 99 k $\Omega$    | 600 kHz  | 2       | 1.05 V |
| 22 | 105.5 k $\Omega$ | 1.2 MHz  | 3       | 0 V    |
| 23 | 112.5 k $\Omega$ | 1.1 MHz  | 3       | 0 V    |
| 24 | 119.6 k $\Omega$ | 1.0 MHz  | 3       | 0 V    |
| 25 | 127 k $\Omega$   | 900 kHz  | 3       | 0 V    |
| 26 | 134.8 k $\Omega$ | 800 kHz  | 3       | 0 V    |
| 27 | 143 k $\Omega$   | 700 kHz  | 3       | 0 V    |
| 28 | 151.4 k $\Omega$ | 600 kHz  | 3       | 0 V    |
| 29 | 160.3 k $\Omega$ | 700kHz   | 0       | 1.05 V |
| 30 | 169.5 k $\Omega$ | 700kHz   | 1       | 1.05 V |
| 31 | 180 k $\Omega$   | 700 kHz  | 2       | 0 V    |
| 32 | 210 k $\Omega$   | 700 kHz  | 3       | 1.05 V |

### Remote Sense Error Amplifier

A high performance, high input impedance, true differential transconductance amplifier is provided to accurately sense the regulator output voltage and provide high bandwidth transient performance. The VSP and VSN inputs should be connected to the regulator's output voltage sense points through filter networks describe in the Droop Compensation and DAC Feed-Forward Compensation sections. The remote sense error amplifier outputs a current proportional to the difference between the output voltage and the DAC voltage:

$$I_{\text{COMP}} = g_m \cdot (V_{\text{DAC}} - (V_{\text{VSP}} - V_{\text{VSN}})) \quad (\text{eq. 1})$$

This current is applied to a standard Type II compensation network.

### Single-Phase Rail Voltage Compensation

The Remote Sense Amplifier outputs a current that is applied to a Type II compensation network formed by external tuning components CLF, RZ and CHF.

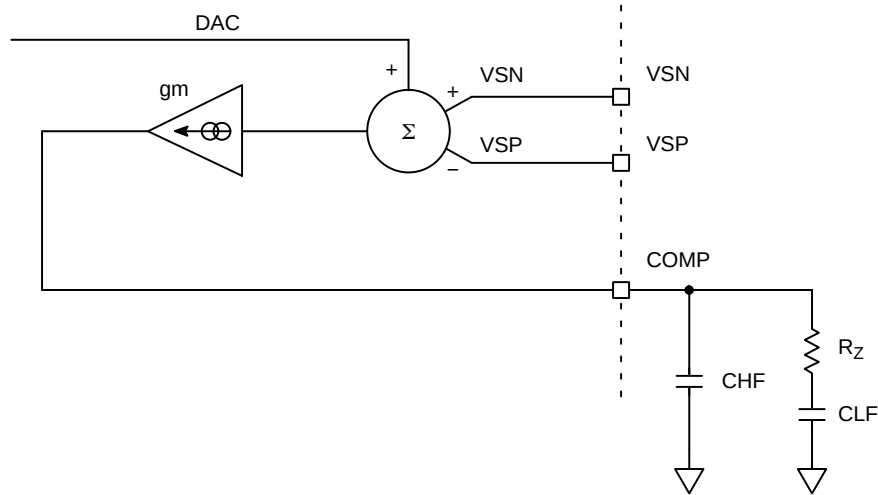


Figure 5.

### Differential Current Feedback Amplifier

The NCP81255 controller has a low offset, differential amplifier to sense output inductor current. An external low-pass filter can be used to superimpose a reconstruction of the AC inductor current onto the DC current signal sensed across the inductor. The low-pass filter time constant should match the inductor L/DCR time constant by setting the filter pole frequency equal to the zero of the output inductor. This makes the filter AC output mimic the product of AC inductor current and DCR, with the same gain as the filter DC output. It is best to perform fine tuning of the filter pole during transient testing.

$$F_Z = \frac{\text{DCR @ 25}^\circ\text{C}}{2 \cdot \pi \cdot L} \quad (\text{eq. 2})$$

$$F_P = \frac{1}{2 \cdot \pi \cdot \left( \frac{R_{\text{PHSP}} \cdot (R_{\text{TH}} + R_{\text{CSSP}})}{R_{\text{PHSP}} + R_{\text{TH}} + R_{\text{CSSP}}} \right) \cdot C_{\text{CSSP}}} \quad (\text{eq. 3})$$

Forming the low-pass filter with an NTC thermistor ( $R_{\text{TH}}$ ) placed near the output inductor, compensates both the DC gain and the filter time constant for the inductor DCR change with temperature. The values of  $R_{\text{PHSP}}$  and  $R_{\text{CSSP}}$  are set

based on the effect of temperature on both the thermistor and inductor. The CSP and CSN pins are high impedance inputs, but it is recommended that the low-pass filter resistance not exceed 10 k $\Omega$  in order to avoid offset due to leakage current. It is also recommended that the voltage sense element (inductor DCR) be no less than 0.5 m $\Omega$  for sufficient current accuracy. Recommended values for the external filter components are:

$$\begin{aligned} R_{\text{PHSP}} &= 7.68 \text{ k}\Omega \\ R_{\text{CSSP}} &= 14.3 \text{ k}\Omega \\ R_{\text{TH}} &= 100 \text{ k}\Omega, \text{ Beta} = 4300 \end{aligned}$$

$$C_{\text{CSSP}} = \frac{L_{\text{PHASE}}}{\frac{R_{\text{PHSP}} \cdot (R_{\text{TH}} + R_{\text{CSSP}})}{R_{\text{PHSP}} + R_{\text{TH}} + R_{\text{CSSP}}} \cdot \text{DCR}} \quad (\text{eq. 4})$$

Using 2 parallel capacitors in the low-pass filter allows fine tuning of the pole frequency using commonly available capacitor values.

The DC gain equation for the current sense amplifier output is:

$$V_{\text{CURR}} = \frac{R_{\text{TH}} + R_{\text{CSSP}}}{R_{\text{PHSP}} + R_{\text{TH}} + R_{\text{CSSP}}} \cdot I_{\text{OUT}} \cdot \text{DCR} \quad (\text{eq. 5})$$

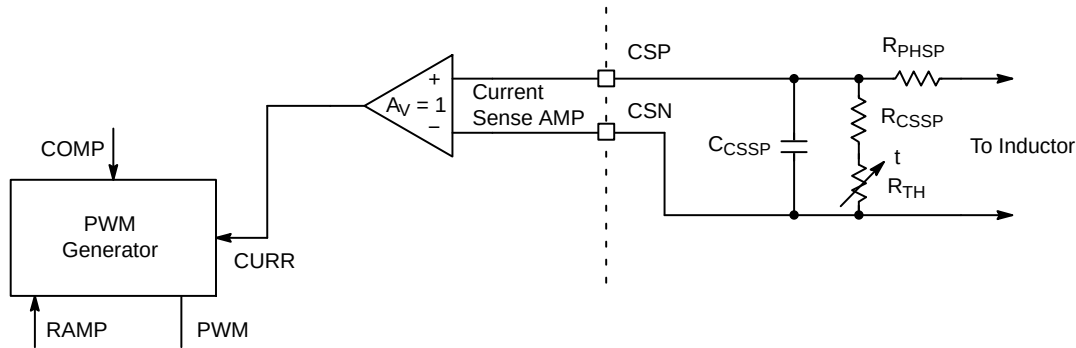


Figure 6.

The amplifier output signal is combined with the COMP and RAMP signals at the PWM comparator inputs to produce the Ramp Pulse Modulation (RPM) PWM signal.

### PSYS

The PSYS pin is an analog input to the NCP81255. It is a system input power monitor that facilitates the monitoring of the total platform system power. For more details about PSYS please contact Intel, Inc.

### Load-line Programming (DROOP)

An output load-line is a power supply characteristic wherein the regulated (DC) output voltage decreases by a voltage  $V_{DROOP}$  proportional to load current. This characteristic can reduce the output capacitance required to maintain output voltage within limits during load transients faster than those to which the regulation loop can respond.

In the NCP81255, a load-line is produced by adding a signal proportional to output load current ( $V_{DROOP}$ ) to the output voltage feedback signal – thereby satisfying the voltage regulator at an output voltage reduced proportional to load current.  $V_{DROOP}$  is developed across a resistance between the VSP pin and the output voltage sense point.

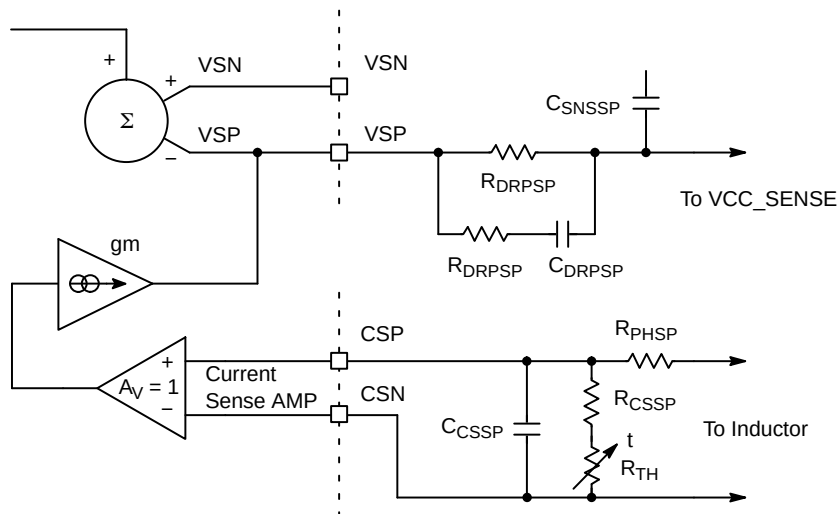


Figure 7.

$$V_{DROOP} = R_{DRPSP} \cdot gm \cdot \frac{R_{TH} + R_{CSSP}}{R_{PHSP} + R_{TH} + R_{CSSP}} \cdot I_{OUT} \cdot DCR \quad (\text{eq. 6})$$

The load-line is programmed by choosing  $R_{DRPSP}$  such that the ratio of voltage produced across  $R_{DRPSP}$  to output current is equal to the desired load-line.

$$R_{DRPSP} = \frac{\text{Loadline}}{gm \cdot DCR} \cdot \frac{R_{PHSP} + R_{TH} + R_{CSSP}}{R_{TH} + R_{CSSP}} \quad (\text{eq. 7})$$

### ICC Max

A resistor to ground on the IMAX pin programs these registers at the time the part is enabled. 10  $\mu\text{A}$  is sourced from these pins to generate a voltage on the program resistor. The resistor value should be no less than 10 k $\Omega$ .

$$ICC\_MAX_{21h} = \frac{R \cdot 10 \mu\text{A} \cdot 255 \text{ A}}{2 \text{ V}} \quad (\text{eq. 8})$$

### Programming IOUT

The IOUT pin sources a current in proportion to the ILIMIT sink current. The voltage on the IOUT pin is monitored by the internal A/D converter and should be

scaled with an external resistor to ground such that a load equal to ICC\_MAX generates a 2 V signal on IOUT. A pull-up resistor from 5 V VCC can be used to offset the IOUT signal positive if needed.

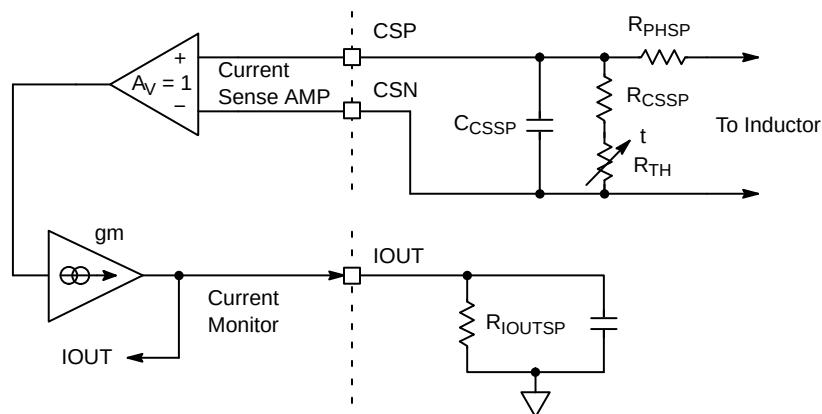


Figure 8.

$$R_{IOUTSP} = \frac{2 \text{ V}}{gm \cdot \frac{R_{TH} + R_{CSSP}}{R_{PHSP} + R_{TH} + R_{CSSP}} \cdot I_{CCMax} \cdot DCR} \quad (\text{eq. 9})$$

### Programming the DAC Feed-Forward Filter

The NCP81255 outputs a pulse of current from the VSN pin upon each increment of the internal DAC following a DVID UP command. A parallel RC network inserted into the path from VSN to the output voltage return sense point, VSS\_SENSE, causes these current pulses to temporarily decrease the voltage between VSP and VSN. This causes the output voltage during DVID to be regulated slightly higher,

in order to compensate for the response of the Droop function to the inductor current flowing into the charging output capacitors. RFFSP sets the gain of the DAC feed-forward and CFFSP provides the time constant to cancel the time constant of the system per the following equations. C<sub>OUT</sub> is the total output capacitance of the system.

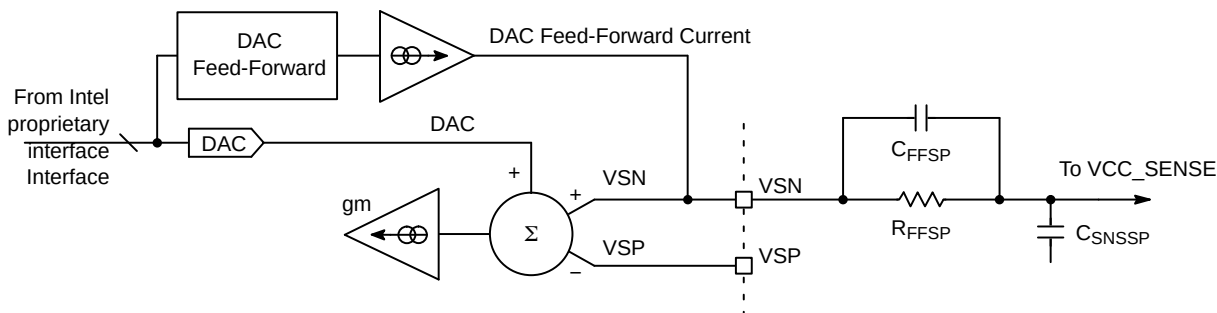


Figure 9.

$$R_{FFSP} = \frac{\text{Loadline} \cdot C_{OUT}}{1.35 \cdot 10^{-9}} \quad (\Omega) \quad C_{FFSP} = \frac{200}{R_{FFSP}} \quad (\text{nF}) \quad (\text{eq. 10})$$

### Programming the Current Limit

The current limit threshold is programmed with a resistor ( $R_{ILIM}$ ) from the ILIM pin to ground. The current limit latches the single-phase rail off immediately if the ILIM pin voltage exceeds the ILIM Threshold. Set the value of the

current limit resistor based on the equation shown below. A capacitor can be placed in parallel with the programming resistor to slightly delay activation of the latch if some tolerance of short over-current events is desired.

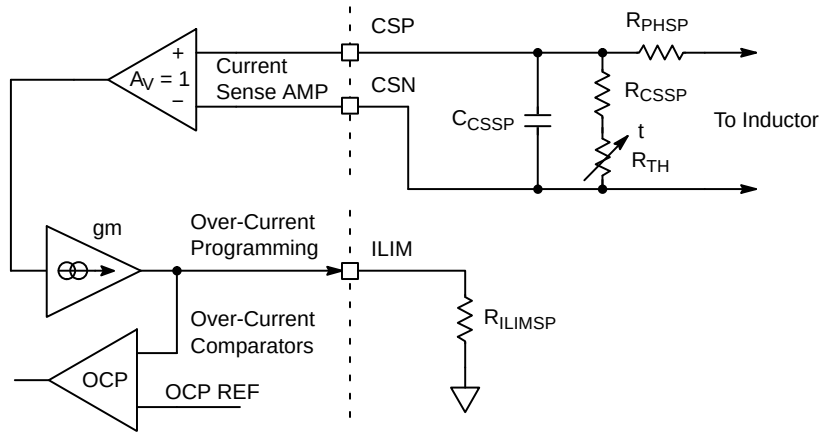


Figure 10.

$$R_{ILIMSP} = \frac{1.3 \text{ V}}{gm \cdot \frac{R_{TH} + R_{CSSP}}{R_{PHSP} + R_{TH} + R_{CSSP}} \cdot I_{OUT\_LIMIT} \cdot DCR} \quad (\text{eq. 11})$$

### TSENSE

A temperature sense input is provided. A precision current is sourced out the TSENSE pin to generate voltage on the temperature sense network. The voltage on the temperature

sense input is sampled by the internal A/D converter. A 100k NTC similar to the VISHAY ERT-J1VS104JA should be used. See the specification table for the thermal sensing voltage thresholds and source current.

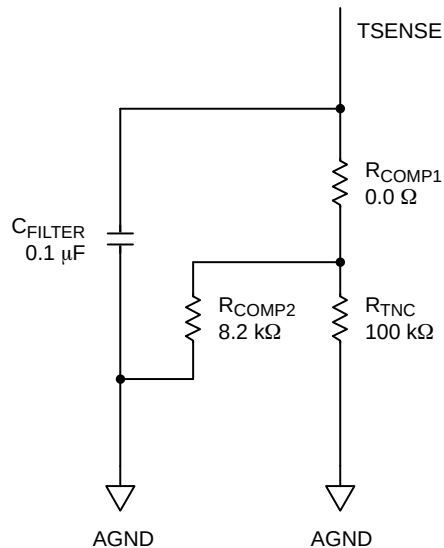


Figure 11.



### Ultrasonic Mode

The switching frequency of a rail in DCM will decrease at very light loads. Ultrasonic Mode forces the switching frequency to stay above the audible range.

### Input Under-Voltage Protection

The controller is protected against under-voltage on the VCC, VCCP, and VFF pins.

### Under-Voltage Protection

Under-voltage protection will shut off the output similar to OCP to protect against short circuits. The threshold is specified in the parametric spec tables and is not adjustable.

### Over-Current Protection (OCP)

A programmable current limit is programmed with a resistor between the ILIM pin and ground. To this resistor is compared to the ILIM Threshold Voltage ( $V_{CL}$ ). If the ILIM pin voltage exceeds the lower Threshold Voltage, an internal latch-off timer starts. When the timer expires, the controller shuts down if the fault is not removed. If the voltage at the ILIM pin exceeds the higher Threshold Voltage, the controller shuts down immediately. To recover from an OCP fault, the EN pin or  $V_{CC}$  voltage must be cycled low.

### Layout Notes

The NCP81255 has differential voltage and current monitoring. This improves signal integrity and reduces noise issues related to layout for easy design use. To insure proper function there are some general rules to follow. Always place the inductor current sense RC filters as close to the CSN and CSP pins on the controller as possible. Place the VCC decoupling caps as close as possible to the controller VCC pin.

### Electrical Layout Considerations

Good electrical layout is a key to make sure proper operation, high efficiency, and noise reduction. Electrical layout guidelines are:

- **Power Paths:** Use wide and short traces for power paths (such as VIN, VOUT, SW, and PGND) to reduce parasitic inductance and high-frequency loop area. It is also good for efficiency improvement.
- **Power Supply Decoupling:** The device should be well decoupled by input capacitors and input loop area should be as small as possible to reduce parasitic inductance, input voltage spike, and noise emission. Usually, a small low-ESL MLCC is placed very close to VIN and PGND pins.
- **VCC Decoupling:** Place decoupling caps as close as possible to the controller VCC and VCCP pins. The filter resistor at VCC pin should be not higher than  $2.2\ \Omega$  to prevent large voltage drop.

- **Switching Node:** SW node should be a copper pour, but compact because it is also a noise source.
- **Bootstrap:** The bootstrap cap and an optional resistor need to be very close and directly connected between BST and SW pins. No need to externally connect pin 10 to SW node because it has been internally connected to other SW pins.
- **Ground:** It would be good to have separated ground planes for PGND and GND and connect the two planes at one point. Directly connect GND pin to the exposed panda then connect to GND ground plane through vias.
- **Voltage Sense:** Use Kelvin sense pair and arrange a “quiet” path for the differential output voltage sense.
- **Current sense:** Careful layout for current sensing is critical for jitter minimization, accurate current limiting, and IOUT reporting. The temperature compensating thermistor should be placed as close as possible to the inductor. The wiring path should be kept as short as possible and well away from the switch node.
- **Intel proprietary interface Bus:** The Serial VID bus is a high-speed data bus and the bus routing should be done to limit noise coupling from the switching node. The signals should be routed with the Alert# line in between the Intel proprietary interface clock and Intel proprietary interface data lines. The Intel proprietary interface lines must be ground referenced and each line's width and spacing should be such that they have nominal  $50\ \Omega$  impedance with the board stack-up.

### Thermal Layout Considerations

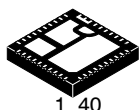
Good thermal layout helps high power dissipation from a small package with reduced temperature rise. Thermal layout guidelines are:

- The exposed pads must be well soldered on the board.
- A four or more layers PCB board with solid ground planes is preferred for better heat dissipation.
- More free vias are welcome to be around IC and underneath the exposed pads to connect the inner ground layers to reduce thermal impedance.
- Use large area copper pour to help thermal conduction and radiation.
- Do not put the inductor too close to the IC, thus the heat sources are distributed.

# MECHANICAL CASE OUTLINE

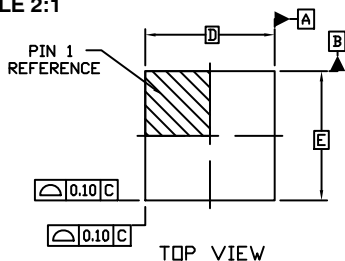
## PACKAGE DIMENSIONS

ON Semiconductor®

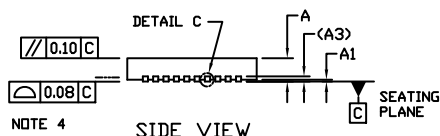


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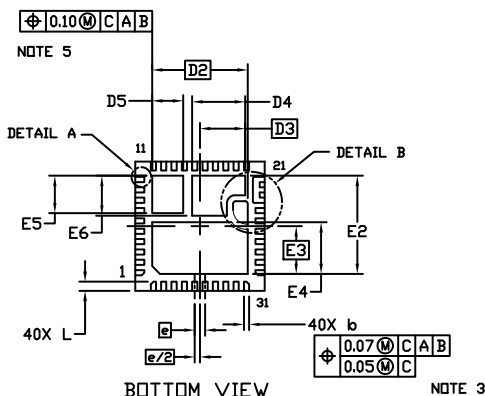
SCALE 2:1



TOP VIEW



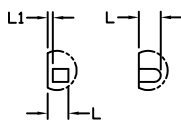
SIDE VIEW



BOTTOM VIEW

### NOTES:

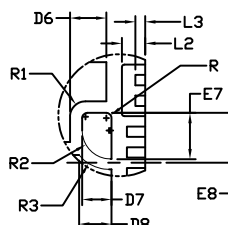
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS
3. DIMENSION b APPLIES TO THE PLATED TERMINAL AND IS MEASURED BETWEEN 0.15 AND 0.30 MM FROM THE TERMINAL TIP.
4. COPLANARITY APPLIES TO THE EXPOSED PAD AS WELL AS THE TERMINALS.
5. POSITIONAL TOLERANCE APPLIES TO ALL OF THE EXPOSED PADS IN BOTH THE X AND Y AXIS.



DETAIL A  
ALTERNATE TERMINAL  
CONSTRUCTIONS



DETAIL C  
ALTERNATE  
CONSTRUCTION

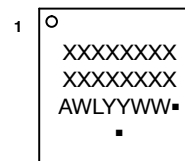


DETAIL B

DATE 26 APR 2016

| DIM | MILLIMETERS |      |
|-----|-------------|------|
|     | MIN.        | MAX. |
| A   | 0.80        | 1.00 |
| A1  | ---         | 0.05 |
| A3  | 0.20        | REF  |
| b   | 0.15        | 0.25 |
| D   | 5.00        | BSC  |
| D2  | 3.70        | BSC  |
| D3  | 1.75        | BSC  |
| D4  | 2.00        | 2.10 |
| D5  | 1.15        | 1.25 |
| D6  | 0.65        | 0.75 |
| D7  | 0.57        | REF  |
| D8  | 0.63        | REF  |
| E   | 5.00        | BSC  |
| E2  | 3.75        | 3.85 |
| E3  | 1.85        | BSC  |
| E4  | 1.95        | 2.05 |
| E5  | 1.40        | 1.50 |
| E6  | 1.50        | 1.60 |
| E7  | 0.89        | REF  |
| E8  | 0.96        | REF  |
| e   | 0.40        | BSC  |
| L   | 0.25        | 0.45 |
| L1  | ---         | 0.15 |
| L2  | 0.35        | 0.55 |
| L3  | 0.10        | 0.30 |
| R   | R0.10       | REF  |
| R1  | R0.30       | REF  |
| R2  | R0.55       | REF  |
| R3  | R0.75       | REF  |

### GENERIC MARKING DIAGRAM\*



XXXXXX = Specific Device Code  
A = Assembly Location  
WL = Wafer Lot  
YY = Year  
WW = Work Week  
▪ = Pb-Free Package

(Note: Microdot may be in either location)

\*This information is generic. Please refer to device data sheet for actual part marking.

Pb-Free indicator, "G" or microdot "▪", may or may not be present.

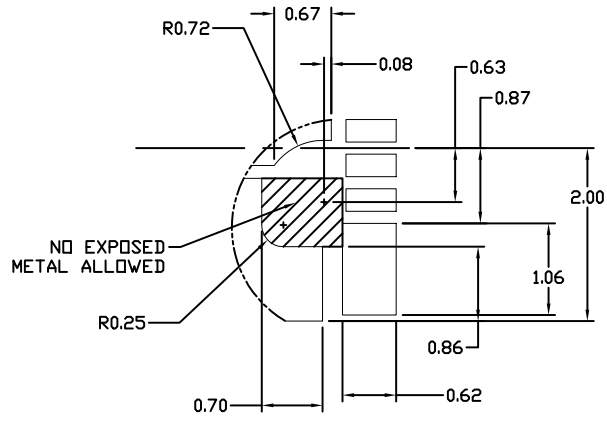
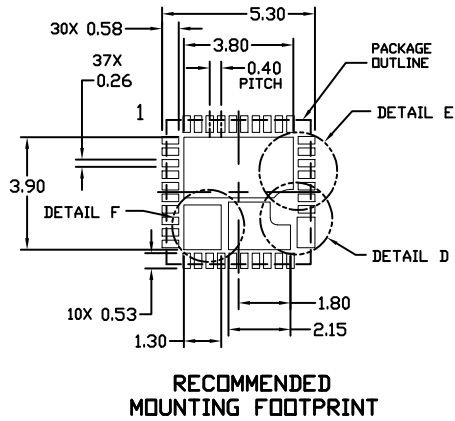
### SOLDERING FOOTPRINT AND VIEWS ON PAGE 2

|                  |                  |                                                                                                                                                                                     |
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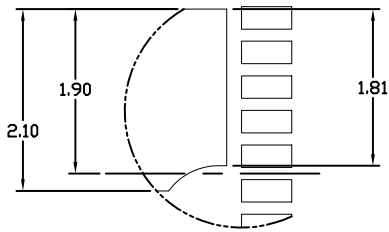
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**QFN40 5x5, 0.4P**  
**CASE 485DY**  
**ISSUE A**

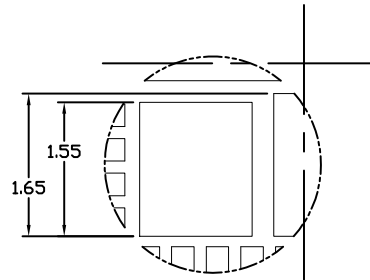
DATE 26 APR 2016



DETAIL D



DETAIL E



DETAIL F

|                         |                         |                                                                                                                                                                                     |
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| <b>DESCRIPTION:</b>     | <b>QFN40, 5x5, 0.4P</b> | <b>PAGE 2 OF 2</b>                                                                                                                                                                  |

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